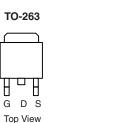
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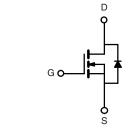


Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0028			
I _D (A)	120			
Configuration	Single			





N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 qualified^d
- 100 % Rg and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION		
Package	TO-263	
Lead (Pb)-free and Halogen-free	SQM110N04-03-GE3	

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current ^a	T _C = 25 °C	1	120		
	T _C = 125 °C	I _D	120		
Continuous Source Current (Diode Conduction) ^a		I _S	120	А	
Pulsed Drain Current ^b		I _{DM}	480		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	70		
Single Pulse Avalanche Energy		E _{AS}	245	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	375	W	
	T _C = 125 °C	P _D	125	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient F	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/W	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 $\mu s,\,duty\,cycle \leq$ 2 %.

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

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PARAMETER	SYMBOL	vise noted) TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		40	-	-		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μΑ	2.5	3.0	3.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1.0		
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 30 A	-	0.0023	0.0028	Ω	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0045		
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0056		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	92	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		= 0 V V _{DS} = 20 V, f = 1 MHz	-	8161	10 205	pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V		-	1353	1695		
Reverse Transfer Capacitance	C _{rss}			-	968	1210		
Total Gate Charge ^c	Qg			-	168	255		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 110 \text{ A}$	-	40.7	-	nC	
Gate-Drain Charge ^c	Q _{gd}]		-	47.1	-		
Gate Resistance	Rg	f = 1 MHz		0.57	1.1	1.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	32	48		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \text{ V}, \text{ R}_L = 0.18 \ \Omega \\ I_D \cong 110 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \ \Omega \end{array}$		-	21	32	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	60	90		
Fall Time ^c	t _f			-	20	30		
Source-Drain Diode Ratings and Chara	acteristics ^b	·						
Pulsed Current ^a	I _{SM}			-	-	480	А	

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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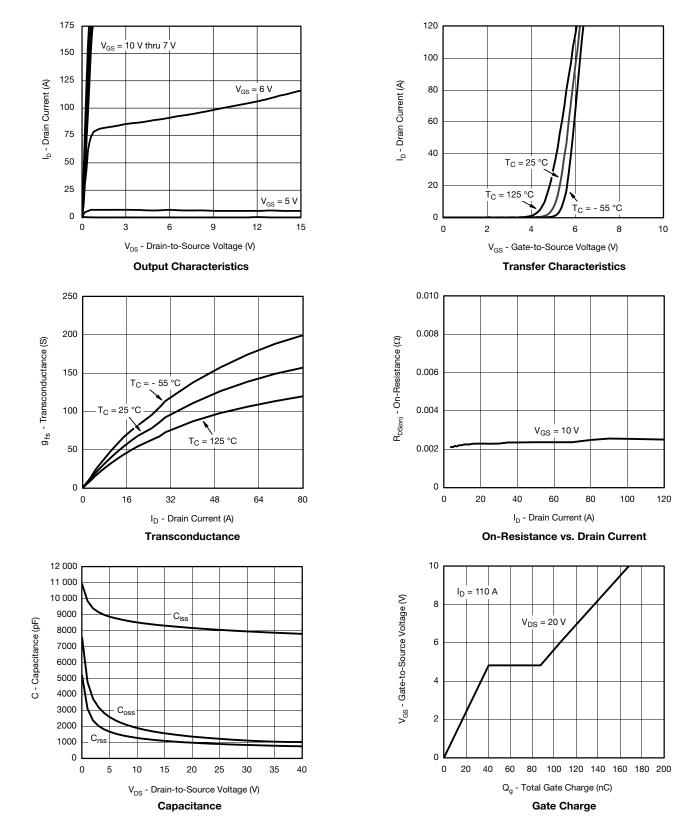
100

120

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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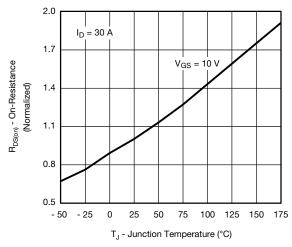
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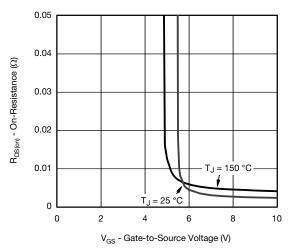
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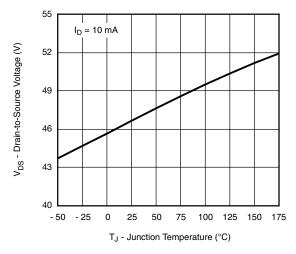
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)







On-Resistance vs. Gate-to-Source Voltage

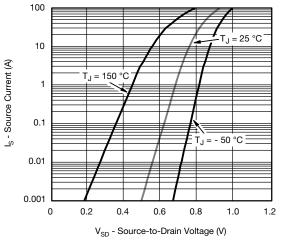


Drain Source Breakdown vs. Junction Temperature

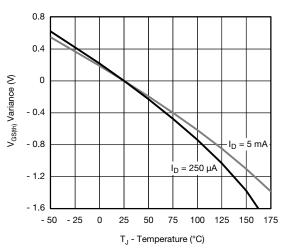
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Source Drain Diode Forward Voltage



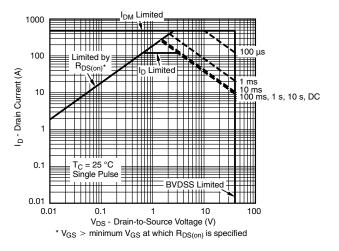
Threshold Voltage



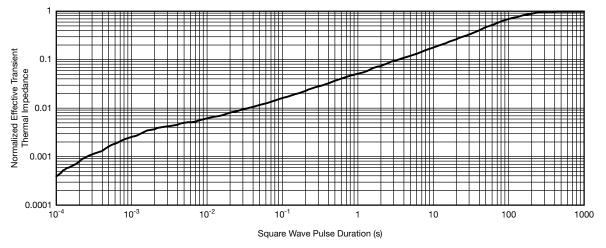
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

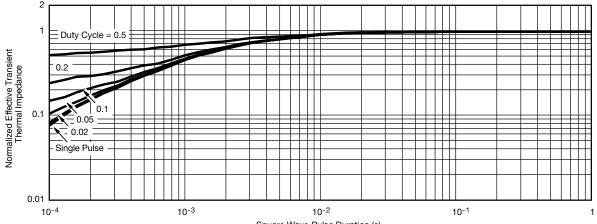
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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